## Description

The F2971 is a high reliability, low insertion loss, $75 \Omega$ absorptive SP2T RF switch designed for a multitude of cable systems and RF applications. This device covers a broad frequency range from 5 MHz to 3000 MHz . In addition to providing low insertion loss, the F2971 also delivers excellent linearity and isolation performance while providing a $75 \Omega$ termination for the unselected port.

The F2971 uses a single positive supply voltage and supports 3.3 V logic.

## Competitive Advantage

The F2971 provides broadband RF performance to support the CATV market along with high power handling and high isolation.

- Low insertion loss
- High isolation
- Excellent linearity
- Extended temperature: $-40^{\circ} \mathrm{C}$ to $+105^{\circ} \mathrm{C}$


## Typical Applications

- CATV/Broadband applications
- Headend
- Fiber/HFC distribution nodes
- Distribution amplifiers
- Switch matrix
- DTV tuner input select
- DVR/PVR/Set-top box
- CATV test equipment


## Features

- Low insertion loss: 0.31 dB at 1200 MHz
- High Isolation: 71 dB at 1200 MHz (RF1/RF2 to RFC)
- High IIP3: 67dBm at 5MHz
- Operating Temperature: $-40^{\circ} \mathrm{C}$ to $+105^{\circ} \mathrm{C}$
- $4 \mathrm{~mm} \times 4 \mathrm{~mm}, 20$-pin LQFN package


## Block Diagram

Figure 1. Block Diagram


## Pin Assignments

Figure 2. Pin Assignments for $4 \mathrm{~mm} \times 4 \mathrm{~mm} \times 0.75 \mathrm{~mm} 20$-pin LQFN, NCG20P1 - Top View


## Pin Descriptions

Table 1. Pin Descriptions

| Number | Name | Description |
| :---: | :---: | :---: |
| $\begin{gathered} 1,2,4,5,6, \\ 7,9,10,11, \\ 12,14,15, \\ 18,19 \end{gathered}$ | GND | Internally grounded. Connect pin directly to paddle ground or as close as possible to the pin with thru-hole vias. |
| 3 | RF1 | RF1 Port. Matched to $75 \Omega$. If this pin is not $0 V \mathrm{DC}$, then an external coupling capacitor must be used. |
| 8 | RFC | RFC Port. Matched to $75 \Omega$. If this pin is not 0 V DC, then an external coupling capacitor must be used. |
| 13 | RF2 | RF2 Port. Matched to $75 \Omega$. If this pin is not $0 V \mathrm{DC}$, then an external coupling capacitor must be used. |
| 16 | C2 | Control pin to set switch state. See Table 8. |
| 17 | C1 | Control pin to set switch state. See Table 8. |
| 20 | $V_{D D}$ | Power Supply. Bypass to GND with capacitors shown in the Typical Application Circuit (see Figure 34) as close as possible to pin. |
|  | EP | Exposed Paddle. Internally connected to GND. Solder this exposed pad to a PCB pad that uses multiple ground vias to provide heat transfer out of the device into the PCB ground planes. These multiple ground vias are also required to achieve the specified RF performance. |

## Absolute Maximum Ratings

Stresses beyond those listed below may cause permanent damage to the device. Functional operation of the device at these or any other conditions beyond those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Table 2. Absolute Maximum Ratings

| Parameter |  | Symbol | Minimum | Maximum | Units |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $V_{D D}$ to GND |  | $V_{D D}$ | -0.3 | 4.0 | V |
| C1, C2 to GND |  | $V_{\text {ctRL }}$ | -0.3 | Lower of $\left(\mathrm{V}_{\mathrm{DD}}+0.3,3.9\right)$ | V |
| RF1, RF2, RFC to GND |  | $V_{\text {RFIN }}$ | -0.3 | +0.3 | V |
| Maximum Input CW Power [a] | RF1 or RF2 as an input (connected to RFC). <br> No RF power applied to unused RF1 or RF2 port. | Pmax-In |  | 30 | dBm |
|  | RFC as an input (connected to RF1 or RF2). No RF power applied to terminated RF1 or RF2 port. |  |  | 30 |  |
|  | RF1 or RF2 port as an input (terminated states). Applied to only one port. |  |  | 26 |  |
|  | RFC as an input (terminated states). No RF drive applied to RF1 or RF2 ports. |  |  | 30 |  |
| Maximum Junction Temperature |  | TJMAX |  | 140 | ${ }^{\circ} \mathrm{C}$ |
| Storage Temperature Range |  | TSTOR | -65 | 150 | ${ }^{\circ} \mathrm{C}$ |
| Lead Temperature (soldering, 10s) |  |  |  | 260 | ${ }^{\circ} \mathrm{C}$ |
| Electrostatic Discharge - HBM (JEDEC/ESDA JS-001-2012) |  |  |  | $\begin{gathered} 1500 \\ \text { (Class 2) } \end{gathered}$ | V |
| Electrostatic Discharge - CDM (JEDEC 22-C101F) |  |  |  | $\begin{gathered} 1500 \\ \text { (Class C3) } \end{gathered}$ | V |

a. Levels based on $\mathrm{V}_{\mathrm{DD}}=2.7 \mathrm{~V}$ to $3.6 \mathrm{~V}, 5 \mathrm{MHz} \leq \mathrm{f}_{\mathrm{RF}} \leq 3000 \mathrm{MHz}, \mathrm{T}_{\mathrm{EP}}=105^{\circ} \mathrm{C}, \mathrm{Z}_{\mathrm{S}}=\mathrm{Z}_{\mathrm{L}}=75 \Omega$.

## Recommended Operating Conditions

Table 3. Recommended Operating Conditions

| Parameter | Symbol | Condition |  | Minimum | Typical | Maximum | Units |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Supply Voltage | $V_{D D}$ |  |  | 2.7 |  | 3.6 | V |
| Operating Temperature Range | $\mathrm{T}_{\text {EP }}$ | Exposed Paddle |  | -40 |  | +105 | ${ }^{\circ} \mathrm{C}$ |
| RF Frequency Range | $\mathrm{f}_{\mathrm{RF}}$ |  |  | 5 |  | 3000 | MHz |
| RF Continuous Input CW Power (Non-Switched) ${ }^{\text {a] }}$ | $\mathrm{P}_{\text {RF }}$ | RFC connected to RF1 or RF2 | $\mathrm{T}_{\text {EP }}=85^{\circ} \mathrm{C}$ |  |  | 27 | dBm |
|  |  |  | $\mathrm{T}_{\mathrm{EP}}=105^{\circ} \mathrm{C}$ |  |  | 27 |  |
|  |  | RF1 / RF2 Input, Terminated State | $\mathrm{T}_{\text {EP }}=85^{\circ} \mathrm{C}$ |  |  | 24 |  |
|  |  |  | $\mathrm{T}_{\mathrm{EP}}=105^{\circ} \mathrm{C}$ |  |  | 21 |  |
| RF Continuous Input Power (RF Hot Switching CW) ${ }^{[a]}$ | Prfsw | RFC Input switching between RF1 and RF2 | $\mathrm{T}_{\text {EP }}=85^{\circ} \mathrm{C}$ |  |  | 21 | dBm |
|  |  |  | $\mathrm{T}_{\mathrm{EP}}=105^{\circ} \mathrm{C}$ |  |  | 21 |  |
|  |  | RF1 or RF2 as input, switched between RFC and Terminated State | $\mathrm{T}_{\text {EP }}=85^{\circ} \mathrm{C}$ |  |  | 17 |  |
|  |  |  | $\mathrm{T}_{E P}=105^{\circ} \mathrm{C}$ |  |  | 17 |  |
| RF1 Port Impedance | $Z_{\text {RF1 }}$ | Single-ended |  |  | 75 |  | $\Omega$ |
| RF2 Port Impedance | ZRF2 | Single-ended |  |  | 75 |  | $\Omega$ |
| RFC Port Impedance | $\mathrm{Z}_{\text {RFC }}$ | Single-ended |  |  | 75 |  | $\Omega$ |

a. Levels based on $V_{D D}=2.7 \mathrm{~V}$ to $3.6 \mathrm{~V}, 5 \mathrm{MHz} \leq f_{R F} \leq 3000 \mathrm{MHz}, Z_{S}=Z_{L}=75 \Omega$. See Figure 3 for power handling de-rating vs. RF frequency.

Figure 3. Maximum RF Input Operating Power vs. RF Frequency


## Renesns

## Electrical Characteristics

Table 4. Electrical Characteristics
See the Typical Application Circuit in Figure 34. $\mathrm{V}_{\mathrm{DD}}=3.0 \mathrm{~V}, \mathrm{~T}_{\mathrm{EP}}=+25^{\circ} \mathrm{C}, \mathrm{f}_{\mathrm{RF}}=1200 \mathrm{MHz}$, driven port $=\mathrm{RF} 1$ or $\mathrm{RF} 2, \mathrm{P}_{\mathbb{I N}}=0 \mathrm{dBm}, \mathrm{Z}_{\mathrm{S}}=\mathrm{Z}_{\mathrm{L}}=75 \Omega$. PCB board trace and connector losses are de-embedded, unless otherwise noted.

| Parameter | Symbol | Condition | Minimum | Typical | Maximum | Units |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Logic Input HIGH [a] | $\mathrm{V}_{\text {IH }}$ | $2.7 \mathrm{~V} \leq \mathrm{V}_{\mathrm{DD}} \leq 3.6 \mathrm{~V}$ | $0.7 \times \mathrm{V}_{\text {D }}{ }^{[b]}$ |  | $V_{D D}$ | V |
| Logic Input LOW [a] | $\mathrm{V}_{\text {IL }}$ |  | -0.3 |  | $0.3 \times \mathrm{V}_{\text {D }}$ | V |
| Logic Current | $\mathrm{I}_{\mathrm{H},} \mathrm{l}_{\mathrm{IL}}$ | For each control pin |  | 5 | 500 [c] | nA |
| $V_{D D}$ DC Current [a] | $I_{\text {DD }}$ | Logic inputs at GND or $\mathrm{V}_{\mathrm{DD}}$ |  | 20 | 30 | $\mu \mathrm{A}$ |
| Insertion Loss | IL | $5 \mathrm{MHz} \leq \mathrm{f}_{\text {RF }} \leq 250 \mathrm{MHz}$ |  | 0.22 |  | dB |
|  |  | $250 \mathrm{MHz}<\mathrm{f}_{\mathrm{RF}} \leq 750 \mathrm{MHz}$ |  | 0.26 |  |  |
|  |  | $750 \mathrm{MHz}<\mathrm{f}_{\mathrm{RF}} \leq 1000 \mathrm{MHz}$ |  | 0.29 |  |  |
|  |  | $1000 \mathrm{MHz}<\mathrm{ffF} \leq 1200 \mathrm{MHz}$ [d] |  | 0.31 | 0.51 |  |
|  |  | $1200 \mathrm{MHz}<\mathrm{f}_{\mathrm{RF}} \leq 2000 \mathrm{MHz}$ |  | 0.47 |  |  |
|  |  | $2000 \mathrm{MHz}<\mathrm{f}_{\mathrm{RF}} \leq 3000 \mathrm{MHz}$ |  | 0.64 |  |  |
| Isolation (RF1/RF2 to RFC) | ISORFC | $5 \mathrm{MHz} \leq \mathrm{f}_{\mathrm{RF}} \leq 250 \mathrm{MHz}$ | 76 | 81 |  | dB |
|  |  | $250 \mathrm{MHz}<\mathrm{f}_{\mathrm{RF}} \leq 750 \mathrm{MHz}$ | 68 | 73 |  |  |
|  |  | $750 \mathrm{MHz}<\mathrm{f}_{\mathrm{RF}} \leq 1000 \mathrm{MHz}$ | 67 | 72 |  |  |
|  |  | $1000 \mathrm{MHz}<\mathrm{f}_{\mathrm{RF}} \leq 1200 \mathrm{MHz}$ | 66 | 71 |  |  |
|  |  | $1200 \mathrm{MHz}<\mathrm{f}_{\mathrm{RF}} \leq 2000 \mathrm{MHz}$ | 60 | 65 |  |  |
|  |  | $2000 \mathrm{MHz}<\mathrm{f}_{\mathrm{RF}} \leq 3000 \mathrm{MHz}$ |  | 57 |  |  |
| Isolation <br> (RF1 to RF2 or RF2 to RF1) | $\mathrm{ISO}_{\mathrm{R} 12}$ | $5 \mathrm{MHz} \leq \mathrm{f}_{\mathrm{RF}} \leq 250 \mathrm{MHz}$ | 77 | 84 |  | dB |
|  |  | $250 \mathrm{MHz}<\mathrm{f}_{\mathrm{RF}} \leq 750 \mathrm{MHz}$ | 69 | 74 |  |  |
|  |  | $750 \mathrm{MHz}<\mathrm{f}_{\mathrm{RF}} \leq 1000 \mathrm{MHz}$ | 66 | 71 |  |  |
|  |  | $1000 \mathrm{MHz}<\mathrm{f}_{\mathrm{RF}} \leq 1200 \mathrm{MHz}$ | 64 | 69 |  |  |
|  |  | $1200 \mathrm{MHz}<\mathrm{f}_{\mathrm{RF}} \leq 2000 \mathrm{MHz}$ | 56 | 61 |  |  |
|  |  | $2000 \mathrm{MHz}<\mathrm{f}_{\mathrm{RF}} \leq 3000 \mathrm{MHz}$ |  | 52 |  |  |
| RF1, RF2, RFC Return Loss (Insertion Loss State) | RLIL | $5 \mathrm{MHz} \leq \mathrm{f}_{\mathrm{RF}} \leq 250 \mathrm{MHz}$ |  | 30 |  | dB |
|  |  | $250 \mathrm{MHz}<\mathrm{ffF} \leq 750 \mathrm{MHz}$ |  | 22 |  |  |
|  |  | $750 \mathrm{MHz}<\mathrm{ffF} \leq 1000 \mathrm{MHz}$ |  | 20 |  |  |
|  |  | $1000 \mathrm{MHz}<\mathrm{f}_{\mathrm{RF}} \leq 1200 \mathrm{MHz}$ |  | 18 |  |  |
|  |  | $1200 \mathrm{MHz}<\mathrm{f}_{\mathrm{RF}} \leq 2000 \mathrm{MHz}$ |  | 14 |  |  |
|  |  | $2000 \mathrm{MHz}<\mathrm{f}_{\mathrm{RF}} \leq 3000 \mathrm{MHz}$ |  | 12 |  |  |

a. Increased $I_{D D}$ current will result if logic LOW level is above ground and up to $\mathrm{V}_{\mathrm{IL}}$ max. Similarly, increased $\mathrm{I}_{\mathrm{DD}}$ current will result if the logic HIGH level is below $\mathrm{V}_{\mathrm{DD}}$ and down to $\mathrm{V}_{\mathbb{I}} \min$.
b. Items in min/max columns that are not bold italics are guaranteed by design characterization.
c. Items in min/max columns in bold italics are guaranteed by test.
d. Minimum or maximum specification guaranteed by test at 1200 MHz and by design characterization over the full frequency range.

## Renesns

## Electrical Characteristics

Table 5. Electrical Characteristics
See the Typical Application Circuit in Figure 34. $V_{D D}=3.0 \mathrm{~V}, T_{E P}=+25^{\circ} \mathrm{C}, \mathrm{f}_{\mathrm{RF}}=1200 \mathrm{MHz}$, driven port $=R F 1$ or $R F 2, \mathrm{P}_{\mathbb{I}}=0 \mathrm{dBm}, \mathrm{Z}_{\mathrm{S}}=\mathrm{Z}_{\mathrm{L}}=75 \Omega$. PCB board trace and connector losses are de-embedded, unless otherwise noted.

| Parameter | Symbol | Condition |  |  | Minimum | Typical | Maximum | Units |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| RF1, RF2, RFC Return Loss (Terminated State) | RLterm | $5 \mathrm{MHz} \leq \mathrm{f}_{\mathrm{RF}} \leq 250 \mathrm{MHz}$ |  |  |  | 28 |  | dB |
|  |  | $250 \mathrm{MHz}<\mathrm{f}_{\mathrm{RF}} \leq 750 \mathrm{MHz}$ |  |  |  | 24 |  |  |
|  |  | $750 \mathrm{MHz}<\mathrm{f}_{\mathrm{RF}} \leq 1000 \mathrm{MHz}$ |  |  |  | 22 |  |  |
|  |  | $1000 \mathrm{MHz}<\mathrm{f}_{\mathrm{RF}} \leq 1200 \mathrm{MHz}$ |  |  |  | 21 |  |  |
|  |  | $1200 \mathrm{MHz}<\mathrm{f}_{\mathrm{RF}} \leq 2000 \mathrm{MHz}$ |  |  |  | 17 |  |  |
|  |  | 2000 MHz < $\mathrm{f}_{\text {RF }} \leq 3000 \mathrm{MHz}$ |  |  |  | 13 |  |  |
| Input 1dB Compression [c] | $\mathrm{IP}_{1 \mathrm{~dB}}$ | $5 \mathrm{MHz} \leq \mathrm{f}_{\mathrm{RF}} \leq 250 \mathrm{MHz}$ |  |  |  | 31 |  | dBm |
|  |  | $250 \mathrm{MHz}<\mathrm{f}_{\mathrm{RF}} \leq 2000 \mathrm{MHz}$ |  |  |  | 32 |  |  |
| Input IP2 <br> (Insertion Loss State) | IIP2 | $\mathrm{P}_{\mathrm{IN}}=+13 \mathrm{dBm} / \text { tone }$ <br> ( $f_{1}+f_{2}$ frequency) | $\begin{aligned} & \mathrm{f}_{1}=5 \mathrm{MHz} \\ & \mathrm{f}_{2}=6 \mathrm{MHz} \end{aligned}$ |  |  | 95 |  | dBm |
|  |  |  | $\begin{aligned} & f_{1}=185 \mathrm{MHz} \\ & \mathrm{f}_{2}=190 \mathrm{MHz} \end{aligned}$ |  |  | 111 |  |  |
|  |  |  | $\begin{aligned} & \mathrm{f}_{1}=895 \mathrm{MHz} \\ & \mathrm{f}_{2}=900 \mathrm{MHz} \end{aligned}$ |  |  | 124 |  |  |
| Input IP3 <br> (Insertion Loss State) | IIP3 | $\mathrm{P}_{\text {IN }}=+13 \mathrm{dBm} /$ tone | $\begin{aligned} & \mathrm{f}_{1}=5 \mathrm{MHz} \\ & \mathrm{f}_{2}=6 \mathrm{MHz} \end{aligned}$ |  |  | 67 |  | dBm |
|  |  |  | $\begin{aligned} & f_{1}=185 \mathrm{MHz} \\ & \mathrm{f}_{2}=190 \mathrm{MHz} \end{aligned}$ |  |  | 75 |  |  |
|  |  |  | $\begin{aligned} & f_{1}=1790 \mathrm{MHz} \\ & \mathrm{f}_{2}=1795 \mathrm{MHz} \end{aligned}$ |  |  | 70 |  |  |
| CTB / CSO |  | 77 and 110 channels, Pout $=44 \mathrm{dBmV}$ |  |  |  | -90 |  | dBc |
| Non-RF Driven Spurious [d] | Spurmax | Out any RF port when externally terminated into $75 \Omega$ |  |  |  | -122 |  | dBm |
| Switching Time [e] | $\mathrm{T}_{\text {sw }}$ | 50\% control to 90\% RF |  |  |  | 2.6 |  | $\mu \mathrm{s}$ |
|  |  | 50\% control to 10\% RF |  |  |  | 1.7 |  |  |
| Maximum Switching Rate [f] | SW ${ }_{\text {RATE }}$ |  |  |  |  |  | 25 | kHz |
| Maximum Video Feed-through on RF Ports | $\mathrm{VID}_{\text {FT }}$ | Peak transient during switching measured with $20 n s$ rise time, 0 V to 3.3 V control pulse |  | Rise |  | 1.1 |  | mV pp |
|  |  |  |  | Fall |  | 2.0 |  |  |

a. Items in min/max columns in bold italics are guaranteed by test.
b. Items in min/max columns that are not bold italics are guaranteed by design characterization.
c. The input 1 dB compression point is a linearity figure of merit. Refer to the "Recommended Operating Conditions" section and Figure 3 for the maximum operating power levels.
d. Spurious due to on-chip negative voltage generator. Spurious fundamental $=$ approximately 2.2 MHz .
e. $f_{R F}=1000 \mathrm{MHz}$.
f. Minimum time required between switching of states $=1$ ( (Maximum Switching Rate).

## Thermal Characteristics

Table 6. Package Thermal Characteristics

| Parameter | Symbol | Value | Units |
| :--- | :---: | :---: | :---: |
| Junction to Ambient Thermal Resistance | $\theta_{\mathrm{JA}}$ | 53 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Junction to Case Thermal Resistance <br> (Case is defined as the exposed paddle) | $\theta_{\mathrm{Jc}}$ | 13.8 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Moisture Sensitivity Rating (Per J-STD-020) |  | MSL 1 |  |

## Typical Operating Conditions (TOCs)

Unless otherwise noted:

- $V_{D D}=+3.0 \mathrm{~V}$
- $Z_{S}=Z_{L}=75 \Omega$
- $\mathrm{T}_{\mathrm{EP}}=25^{\circ} \mathrm{C}$
- $f_{\mathrm{RF}}=1200 \mathrm{MHz}$
- Small signal parameters measured with $P_{\operatorname{IN}}=0 \mathrm{dBm}$.
- Driven port is RF1 or RF2.
- All temperatures are referenced to the exposed paddle.
- Evaluation Kit traces and connector losses are de-embedded.


## Typical Performance Characteristics [1]

Figure 4. Insertion Loss vs. Frequency over Temperature and Vdo [RF1]


Figure 6. Isolation vs. Frequency over Temp. and Vdo [RF1 to RF2, RF1 Selected]


Figure 8. Isolation vs. Frequency over Temp. and Vdd [RF2 to RFC, RF1 Selected]


Figure 5. Insertion Loss vs. Frequency over Temperature and Vdo [RF2]


Figure 7. Isolation vs. Frequency over Temp. and Vdd [RF2 to RF1, RF2 Selected]


Figure 9. Isolation vs. Frequency over Temp. and Vdd [RF1 to RFC, RF2 Selected]


## Renesns

## Typical Performance Characteristics [2]

Figure 10. Isolation vs. Frequency over Temp. and Vdd [RF1 to RFC, All Off]


Figure 12. Isolation vs. Frequency over Temp. and Vod [RF1 to RF2, All Off]


Figure 14. RF1 Return Loss vs. Frequency over Temperature and Vdd [All Off]


Figure 11. Isolation vs. Frequency over Temp. and Vdd [RF2 to RFC, All Off]


Figure 13. RFC Return Loss vs. Frequency over Temperature and Vdd [All Off]


Figure 15. RF2 Return Loss vs. Frequency over Temperature and Vdo [All Off]


## Renesns

## Typical Performance Characteristics [3]

Figure 16. RF1 Return Loss vs. Frequency over Temperature and Vdd [RF1 Selected]


Figure 18. RF1 Return Loss vs. Frequency over Temperature and Vdd [RF2 Selected]


Figure 20. RFC Return Loss vs. Frequency over Temperature and Vdd [RF1 Selected]


Figure 17. RF2 Return Loss vs. Frequency over Temperature and Vdd [RF2 Selected]


Figure 19. RF2 Return Loss vs. Frequency over Temperature and Vdd [RF1 Selected]


Figure 21. RFC Return Loss vs. Frequency over Temperature and Vdd [RF2 Selected]


## Renesns

## Typical Performance Characteristics [4]

Figure 22. Evaluation Board Through-Line Loss vs. Frequency over Temperature


Figure 24. Switching Time Insertion Loss to Isolation


Figure 26. Idd vs. Control Voltage; Vdd $=2.7 \mathrm{~V}$ (C1 set to GND and Vod)


Figure 23. Evaluation Board Through-Line Return Loss vs. Freq. over Temp.


Figure 25. Switching Time Isolation to Insertion Loss


Figure 27. Idd vs. Control Voltage; Vdd $=2.7 \mathrm{~V}$ (C1 set to 0.6 V and 2.1 V )


## Typical Performance Characteristics [5]

Figure 28. Idd vs. Control Voltage; Vdd $=3.0 \mathrm{~V}$ (C1 set to GND and Vod)


Figure 30. Idd vs. Control Voltage; $\mathrm{V}_{\mathrm{dd}}=3.6 \mathrm{~V}$ (C1 set to GND and Vod)


Figure 29. Idd vs. Control Voltage; Vdd $=3.0 \mathrm{~V}$ (C1 set to 0.9 V and 2.1 V )


Figure 31. Idd vs. Control Voltage; $\mathrm{V}_{\mathrm{dD}}=\mathbf{3 . 6 V}$ (C1 set to 0.9 V and 2.7V)


## Evaluation Kit Picture

Figure 32. Top View


Figure 33. Bottom View


## Evaluation Kit / Applications Circuit

Figure 34. Electrical Schematic


Table 7. Bill of Material (BOM)

| Part Reference | QTY | Description | Manufacturer Part \# | Manufacturer |
| :---: | :---: | :--- | :---: | :---: |
| $\mathrm{C} 1-\mathrm{C} 6$ | 0 | Not Installed |  |  |
| C 7 | 1 | $1000 \mathrm{pF} \pm 5 \%, 50 \mathrm{~V}, \mathrm{COG}$ Ceramic Capacitor (0603) | GRM1885C1H102J | Murata |
| R1 - R3 | 3 | $100 \Omega \pm 1 \%, 1 / 10 \mathrm{~W}$, Resistor (0402) | ERJ-2RKF1000X | Panasonic |
| $\mathrm{J} 1-\mathrm{J} 5$ | 5 | Connector Type F | 222181 | Amphenol RF |
| J 8 | 1 | Conn Header Vert 8x2 Pos Gold | $961216-6404-$ AR | 3 M |
| U1 | 1 | SP2T Switch 4mm x 4mm LQFN | F2971NCGK | IDT |
|  | 1 | Printed Circuit Board | F297X EVKIT REV 01 | IDT |

## Control Mode

Table 8. Switch Control Truth Table

| C1 | C2 | RFC - RF1 | RFC - RF2 | 75 2 Terminated Ports |
| :---: | :---: | :---: | :---: | :---: |
| LOW | LOW | OFF | OFF | RFC, RF1, RF2 |
| LOW | HIGH | OFF | ON | RF1 |
| HIGH | LOW | ON | OFF | RF2 |
| HIGH | HIGH | N/A | N/A | N/A |

## Application Information

## Default Start-up

Control pins do not include internal pull-down resistors to logic LOW or pull-up resistors to logic HIGH.

## Power Supplies

A common $V_{c c}$ power supply should be used for all pins requiring DC power. All supply pins should be bypassed with external capacitors to minimize noise and fast transients. Supply noise can degrade the noise figure, and fast transients can trigger ESD clamps and cause them to fail. Supply voltage change or transients should have a slew rate smaller than $1 \mathrm{~V} / 20 \mu \mathrm{~s}$. In addition, all control pins should remain at $0 \mathrm{~V}( \pm 0.3 \mathrm{~V})$ while the supply voltage ramps or while it returns to zero.

## Control Pin Interface

If control signal integrity is a concern and clean signals cannot be guaranteed due to overshoot, undershoot, ringing, etc., the following circuit at the input of each control pin is recommended. This applies to control pins 16 and 17 as shown below.

Figure 35. Control Pin Interface Schematic


## Evaluation Kit (EVKit) Operation

## External Supply Setup

Set up a $\mathrm{V}_{\mathrm{cc}}$ power supply in the voltage range of 2.7 V to 3.6 V with the power supply output disabled.

## Logic Control Setup

External logic control is applied to J8 CTL1 (pins 5 and 7) and CTL2 (pins 9 and 11). See Table 8 for the logic truth table.

## Turn On Procedure

Setup the supplies and EVKIT as noted in the "External Supply Setup" and "Logic Control Setup" sections above.
Enable the $\mathrm{V}_{\mathrm{cc}}$ supply.
Set the desired logic setting to achieve the desired configuration (see Table 8). Note that external control logic should not be applied without $V_{\text {Cc }}$ being present.

## Turn Off Procedure

Set the logic control to OV.
Disable the $\mathrm{V}_{\mathrm{CC}}$ supply.

## Package Drawings

The package outline drawings are appended at the end of this document and are accessible from the link below. The package information is the most current data available and is subject to change without notice or revision of this document. www.idt.com/document/psc/20-qfn-package-outline-drawing-40-x-40-x-075-mm-body-05mm-pitch-epad-206-x-206-mm-ncg20p1

## Marking Diagram

| IDTF29 |
| :--- |
| 71NCGK |
| ZEYWWPBG |
|  |

Line 1 and 2 are the part number.
Line 3 - "ZE" is for the die version.
Line 3 - "YWW" is the last digit of the year plus the work week.
Line 3 - "PBG" denotes the production process.

## Renesns

## Ordering Information

| Orderable Part Number | Package | MSL Rating | Shipping Packaging | Operating Temperature |
| :---: | :--- | :---: | :---: | :---: |
| F2971NCGK | $4 \mathrm{~mm} \times 4 \mathrm{~mm} \times 0.75 \mathrm{~mm} 20-$ LQFN <br> (NCG2OP1) | MSL1 | Tray | $-40^{\circ} \mathrm{C}$ to $+105^{\circ} \mathrm{C}$ |
| F2971NCGK8 | $4 \mathrm{~mm} \times 4 \mathrm{~mm} \times 0.75 \mathrm{~mm}$ 20-LQFN <br> (NCG2OP1) | MSL1 | Reel | $-40^{\circ} \mathrm{C}$ to $+105^{\circ} \mathrm{C}$ |
| F2971EVBI | Evaluation Board |  |  |  |

## Revision History

| Revision | Revision Date |  | Description of Change |
| :---: | :---: | :--- | :--- |
| 0 | $2018-$ April-24 | Initial release. |  |

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